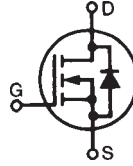


Polar™ Power MOSFET

IXTA1R4N120P
IXTP1R4N120P

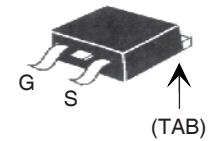
V_{DSS} = 1200V
I_{D25} = 1.4A
R_{DS(on)} ≤ 13Ω

N-Channel Enhancement Mode
Avalanche Rated

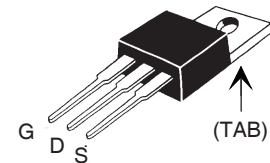


Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	1200	V
V _{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	1200	V
V _{GSS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	1.4	A
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	3.0	A
I _A	T _C = 25°C	1.4	A
E _{AS}	T _C = 25°C	150	mJ
dV/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	10	V/ns
P _D	T _C = 25°C	86	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	1.6mm (0.062) from case for 10s	300	°C
T _{SOLD}	Plastic body for 10s	260	°C
M _d	Mounting torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect

Advantages

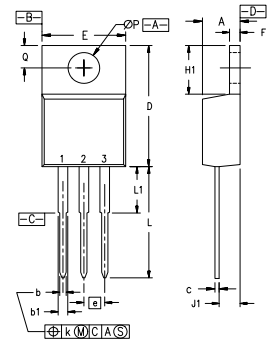
- Easy to mount
- Space savings
- High power density

Applications:

- High Voltage Switched-mode and resonant-mode power supplies
- High Voltage Pulse Power Applications
- High Voltage Discharge circuits in Lasers Pulsers, Spark Igniters, RF Generators
- High Voltage DC-DC converters
- High Voltage DC-AC inverters

Symbol	Test Conditions (T _J = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 250μA	1200		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 100μA	2.5		4.5 V
I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±50 nA
I _{DSS}	V _{DS} = V _{DSS} V _{GS} = 0V T _J = 125°C			5 μA 300 μA
R _{DS(on)}	V _{GS} = 10V, I _D = 0.5 • I _{D25} , Note 1	10.5	13	Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	0.8	1.3	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		666	pF
			36	pF
			7.6	pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 25\Omega$ (External)		25	ns
			27	ns
			78	ns
			29	ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		24.8	nC
			4.4	nC
			12.8	nC
R_{thJC} R_{thCS}	(TO-220)	0.50	1.45 $^\circ\text{C/W}$ $^\circ\text{C/W}$	

TO-220 (IXTP) Outline


Pins: 1 - Gate 2 - Drain

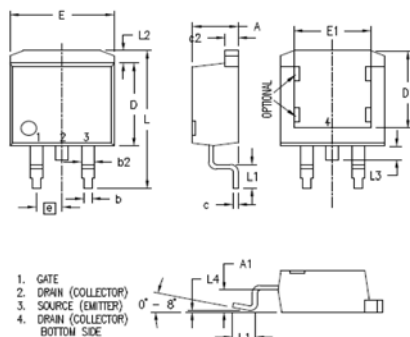
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Source-Drain Diode
Characteristic Values

 ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			1.4 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			4.2 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 1.4\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$		900	ns

 Note 1: Pulse test, $t \leq 300 \mu\text{s}$; duty cycle, $d \leq 2\%$.

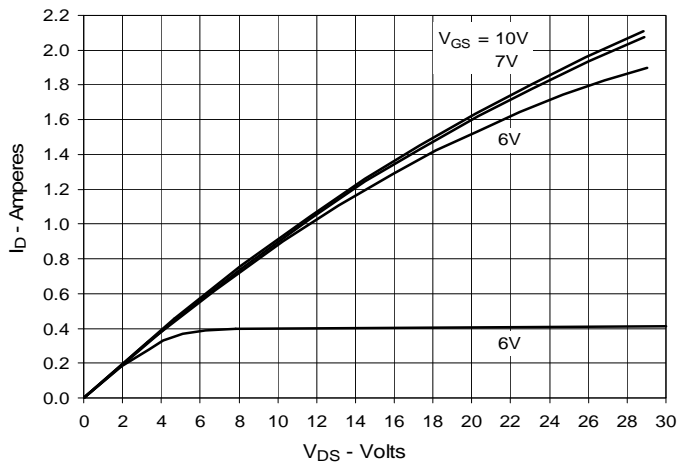
TO-263 (IXTA) Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

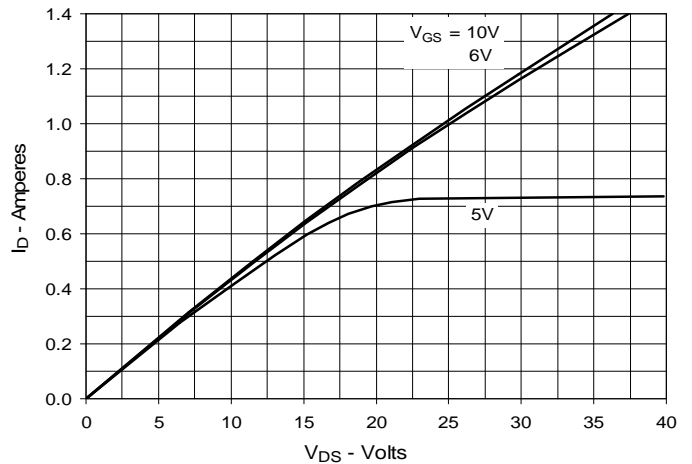
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

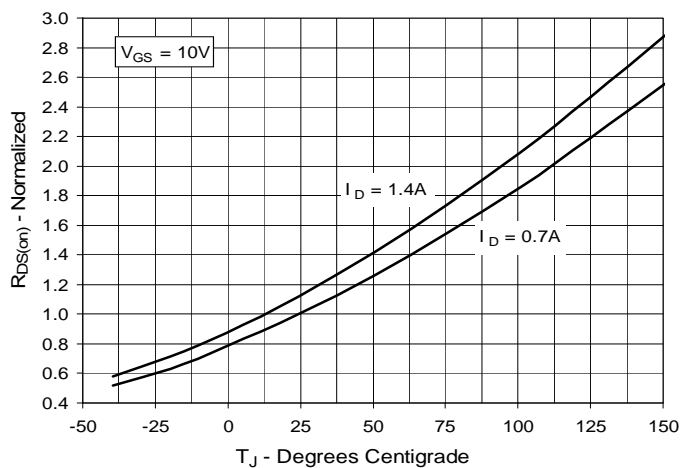
**Fig. 1. Output Characteristics
@ 25°C**



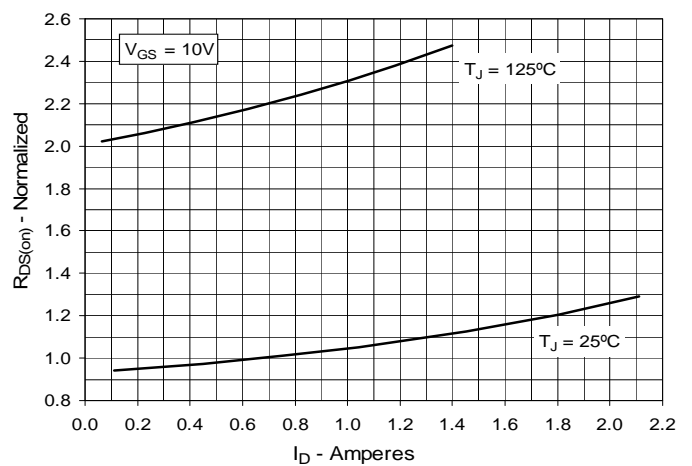
**Fig. 2. Output Characteristics
@ 125°C**



**Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 0.7A$ Value
vs. Junction Temperature**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 0.7A$ Value
vs. Drain Current**



**Fig. 5. Maximum Drain Current vs.
Case Temperature**

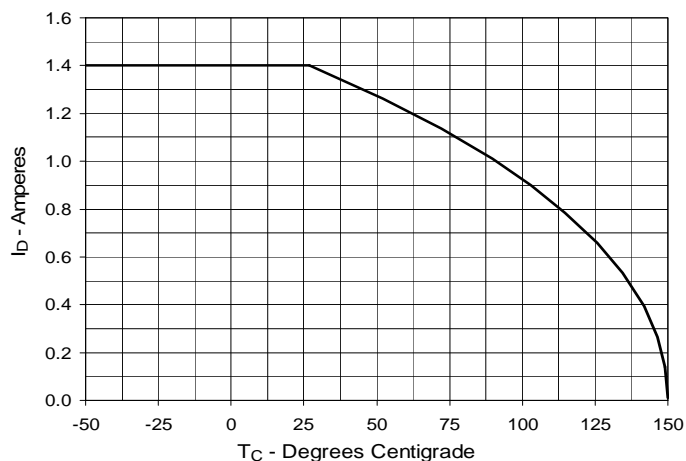


Fig. 6. Input Admittance

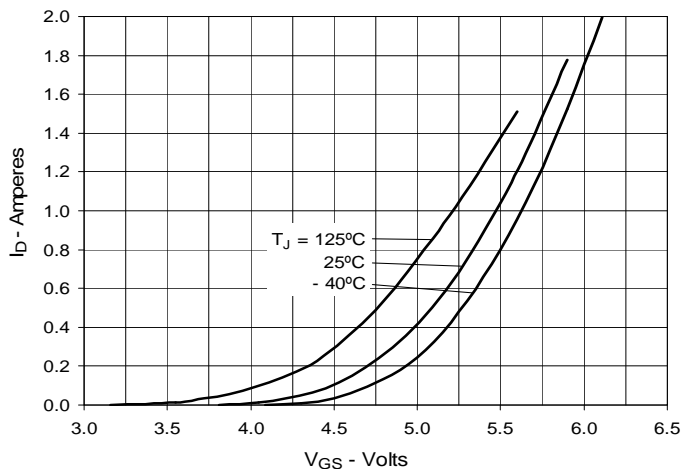


Fig. 7. Transconductance

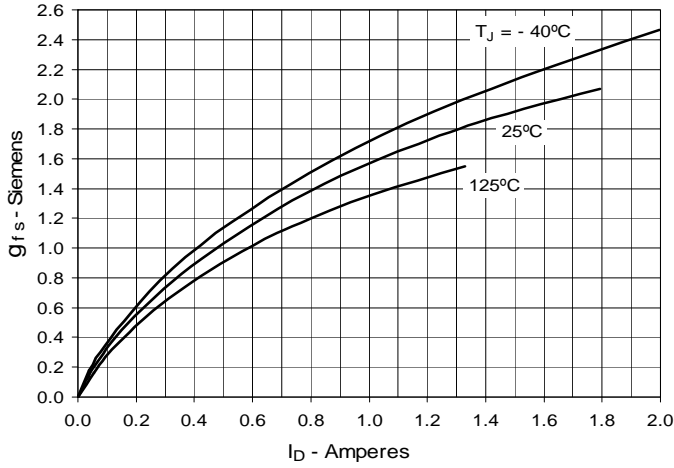


Fig. 8. Forward Voltage Drop of Intrinsic Diode

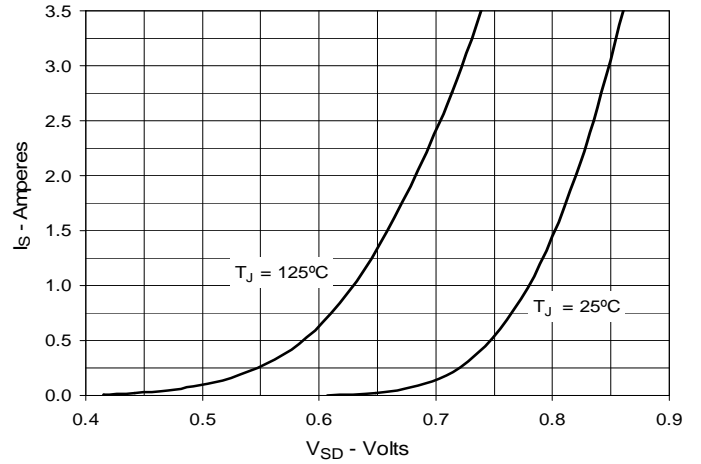


Fig. 9. Gate Charge

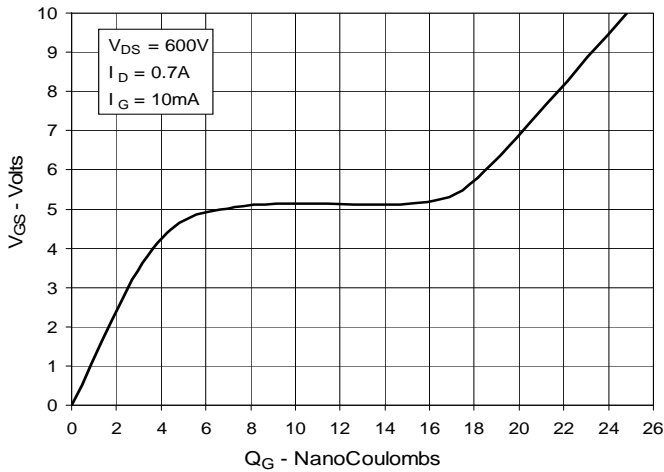


Fig. 10. Capacitance

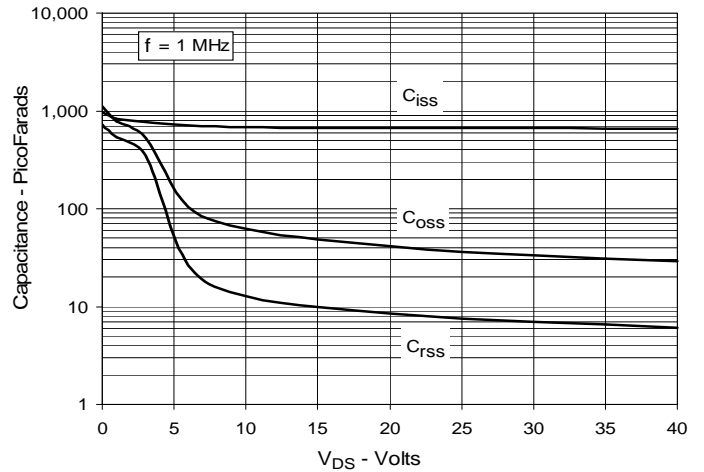


Fig. 11. Maximum Transient Thermal Impedance

